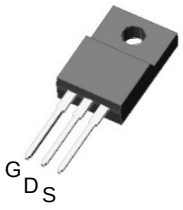
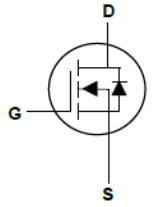
N-Channel Enhancement Mode MOSFET

Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Pin Description

TO-220F	Symbol
	

Applications

- Power Management in Desktop Computer
- DC/DC Converters

V_{DSS}	500	V
$R_{DS(ON)-Typ}$	620	mΩ
I_D	9	A

Absolute Maximum Ratings(T_J=25℃, Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		500	V
V_{GSS}	Gate-Source Voltage		±30	V
T_J	Maximum Junction Temperature		-55 to 150	℃
T_{STG}	Storage Temperature Range		-55 to 150	℃
E_{AS}	Single Pulse Avalanche Energy[3]		250	mJ
I_{DM}[①]	Pulse Drain Current Tested		36	A
I_D	Continuous Drain Current	T_C=25°C	9	A
P_D	Maximum Power Dissipation	T_C=25°C	39	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient[1]	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	3.2	℃/W

Note ①: Max. current is limited by bonding wire.

Note ②: UIS tested and pulse width are limited by maximum junction temperature 150℃.

Note ③: Surface Mounted on 1in^2 FR-4 board with 1oz.

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Electrical Characteristics (T_J=25℃, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	500	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=500V, V_{GS}=0V	---	---	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	2	---	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±30V, V_{DS}=0V	---	---	±0.1	uA
$R_{DS(ON)}$	Drain-Source On-state Resistance	V_{GS}=10V , I_D=9A	---	620	750	mΩ
Dynamic Characteristics⑤						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, Freq.=1MHz	---	820	---	pF
C_{oss}	Output Capacitance		---	6.2	---	
C_{rss}	Reverse Transfer Capacitance		---	110	---	
$T_{d(on)}$	Turn-on Delay Time	V_{DS}=400V , V_{GS}=10V , R_G=25Ω, I_D=9A	---	23	---	nS
T_r	Turn-on Rise Time		---	32	---	
$T_{d(off)}$	Turn-off Delay Time		---	26	---	
T_f	Turn-off Fall Time		---	38	---	
Q_g	Total Gate Charge	V_{DD}=400V , V_{GS}=10V , I_D=9A	---	8.7	---	nC
Q_{gs}	Gate-Source Charge		---	2.6	---	
Q_{gd}	Gate-Drain Charge		---	3.2	---	
Source-Drain Characteristics （T_J=25℃）						
V_{SD}	Diode Forward Voltage②	V_{GS}=0V , I_S=9A ,T_J=25℃	---	0.9	1.2	V
t_{rr}	Reverse Recovery Time	I_F=9A, di/dt=100A/μs, T_J=25℃	---	140	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.5	---	nC

Note ④： Pulse test (pulse width≤300us, duty cycle≤2%).

Note ⑤：Guaranteed by design, not subject to production testing.

Typical Characteristics

Figure 1. Output Characteristics (T_J = 25ºC)

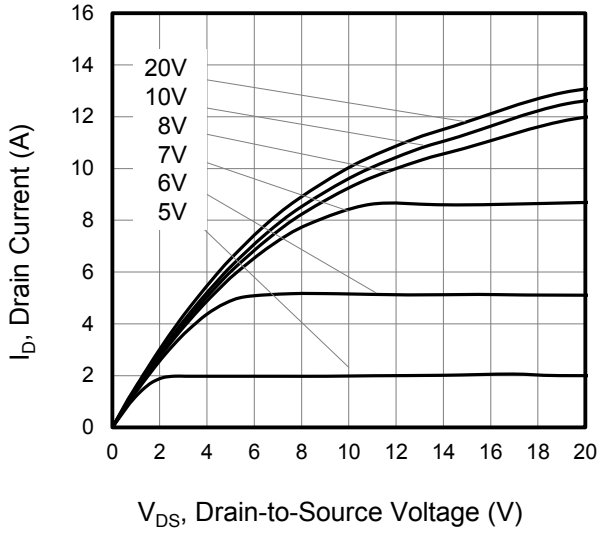

Figure 2. Body Diode Forward Voltage

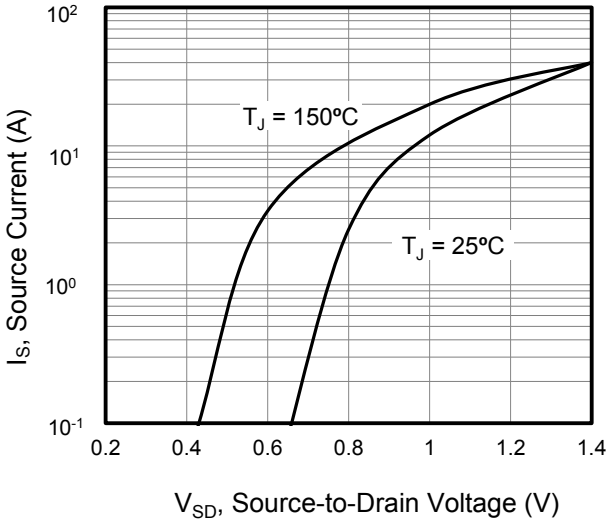

Figure 3. Drain Current vs. Temperature

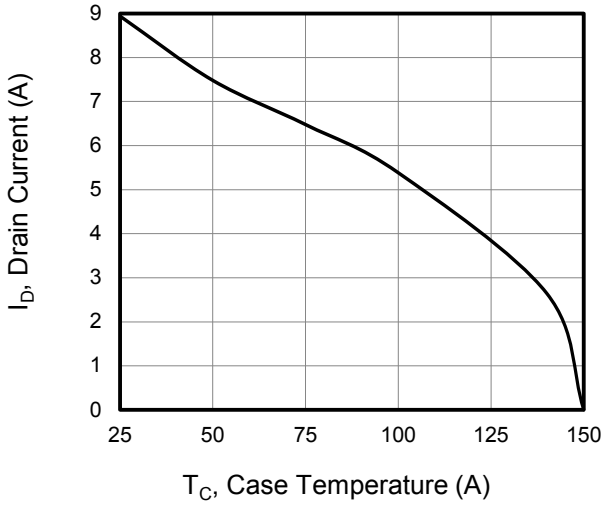

Figure 4. BV_{DSS} Variation vs. Temperature

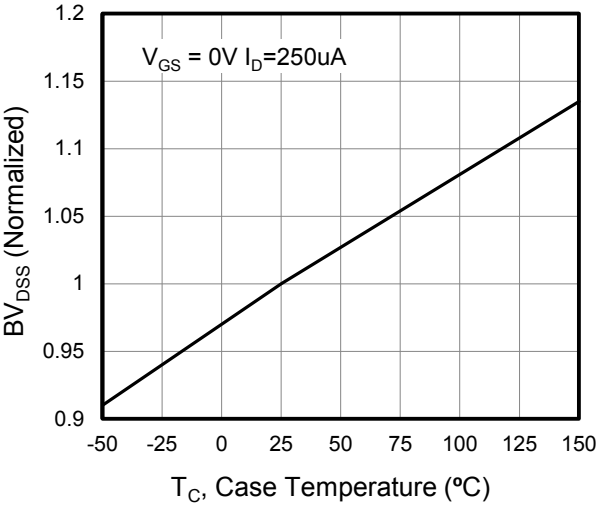

Figure 5. Transfer Characteristics

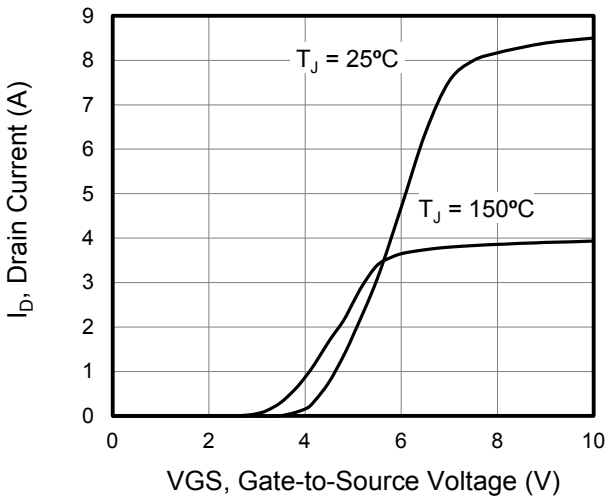

Figure 6. On-Resistance vs. Temperature

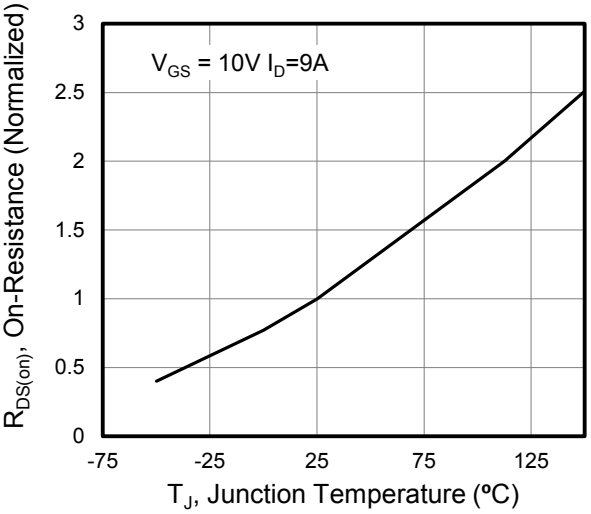

Figure 7. Capacitance

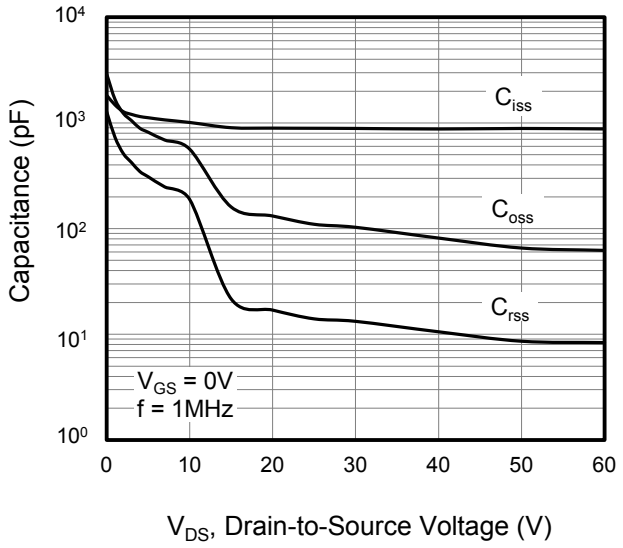

Figure 8. Gate Charge

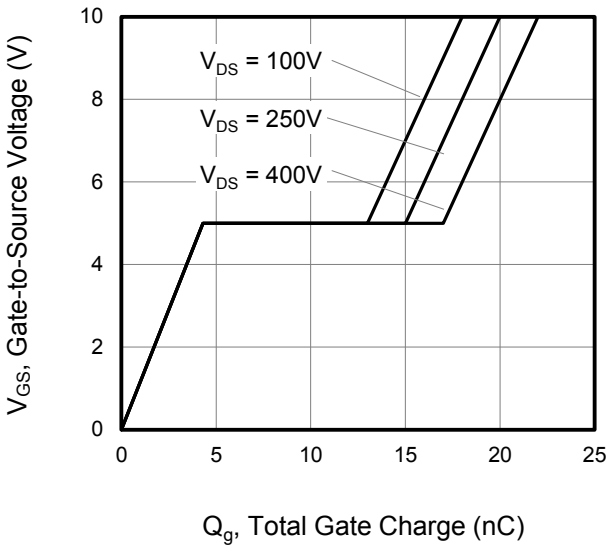

Figure 9. Transient Thermal Impedance

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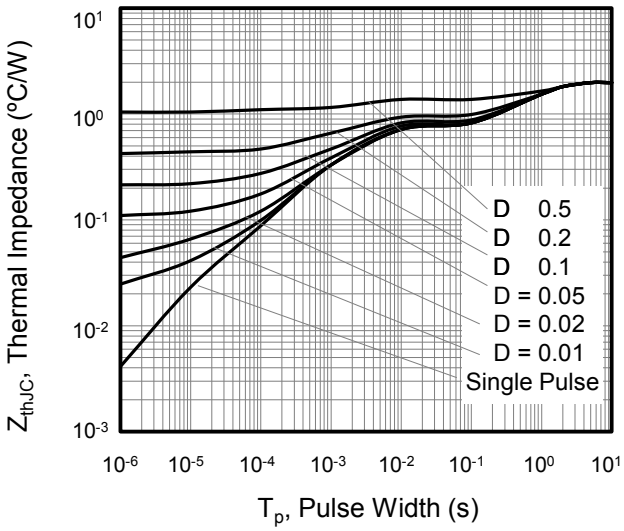

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TO-220F Package Outline Data